## IN THE WHITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No	
Filing Date	
Inventor	Basceri et al.
Assignee	Micron Technology, Inc.
Group Art Unit	1762
Examiner	
Attorney's Docket No	
Title: Chemical Vapor Deposition Metho	ds of Forming Barium Strontium Titanate
Comprising Dielectric Layers	

## **INFORMATION DISCLOSURE STATEMENT**

To:

Mail Stop RCE

**Commissioner for Patents** 

P.O. Box 1450

Alexandria, VA 22313-1450

From:

Jennifer J. Taylor, Ph.D.

(Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

Dear Sir:

The Examiner's attention is directed to the references which are listed on the attached Form PTO-1449 and copies of which are attached.

Citation of these references is respectfully requested.

Respectfully submitted,

Datad:

By:

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Reg. Nov. 48,7/1

ATTY. DOCKET NO. SERIAL NO. MI22-1724 09/905,286 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Form PTO-1449 APPLICANT LIST OF ART CITED BY APPLICANT Cem Basceri et al. FILING DATE **GROUP** JUL 0 9 2004 July 13, 2001 1762 U.S. PATENT DOCUMENTS Filing Date Subclass \*Examiner Date Name If Appropriate АΛ 4,261,698 04/81 Carr et al. AB 09/87 4,691,662 Roppel et al. AC Takasu et al. 5,261,961 11/93 AD 5,270,241 12/93 Dennison et al. ΑE Takasaki et al. 5,312,783 05/94 AF 5,392,189 02/95 Fazan et al. AG 5,395,771 03/95 Nakato ΑH 11/95 5,468,687 Carl et al. ΑI 5,525,156 06/96 Manada et al. 03/97 5,614,018 Azuma et al. AΚ 5,656,329 08/97 Hampden-Smith AL 5,663,089 09/97 Tomozawa et al. FOREIGN PATENT DOCUMENTS Date Class Subclass Translation Document Number Country No AM EP 0 030 798 06/81 EPO AN03/88 GB 2 194 555 A United Kingdom AO 03/89 **EPO** EP 0 306 069 A2 ΑP 09/90 EPO EP 0 388 957 A2 ΛQ IP2250970 10/90 Japan OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) Aoyama et al., Leakage Current Mechanism of Amorphous and Polycrystalline Ta₂O₅ Films Grown by Chemical Vapor Deposition, 143 J. ELECTROCHEM Soc., No. 3, pp 977-983 (March 1996). AS Stemmer et al., Accommodation of nonstoichiometry in (100) fiber-textured (Ba<sub>x</sub>Sr<sub>1-x</sub>)Ti<sub>1+y</sub>O<sub>3+z</sub> thin films grown by chemical vapor deposition, 74 APPL. PHYS. LETT., No. 17, pp. 2432-2434 (26 April 1999). AΤ Streiffer et al., Ferroelectricity in thin films: The dielectric response of fiber-textured (Ba<sub>x</sub>Sr<sub>1.x</sub>)Ti<sub>1+y</sub>O<sub>3+z</sub> thin films grown by chemical vapor deposition, 86 J. APPL. PHYS. No. 8, pp. 4565-4575 (15 October 1999). DATE CONSIDERED EXAMINER \*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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